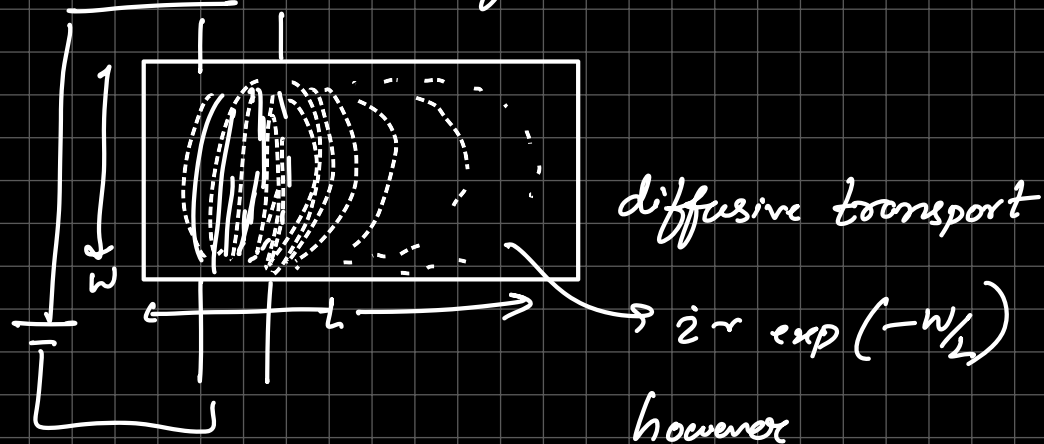


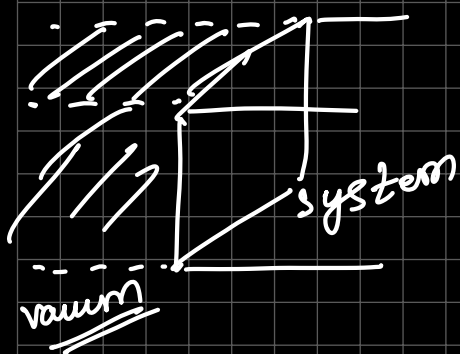
(dec 23 in MD)

some recap of the CdTe-HgTe heterostructure



3 dim Dirac eqn

$$\Delta H_{3D} = v p_y \tau_y + v p_z \alpha_z - B(p_y^2 + p_z^2) \beta$$



$$H_{eff} = \left[\langle \psi_1 |, \langle \psi_2 | \right] \Delta H_{3D} \left[| \psi_1 \rangle, | \psi_2 \rangle \right]^T$$

$$\psi_1 = \begin{pmatrix} \text{sgn} \\ 0 \\ 0 \\ z \end{pmatrix} \left(e^{-x/\xi_+} - e^{-x/\xi_-} \right) e^{i(k_y y + k_z z)}$$

$$\psi_2 = \begin{pmatrix} 0 \\ \text{sgn} B \\ z \\ 0 \end{pmatrix} \left(e^{-x/\xi_+} - e^{-x/\xi_-} \right) e^{i(k_y y + k_z z)}$$

$$\langle \psi_1 | \Delta H_{eff} | \psi_1 \rangle = v p_y \text{sgn}(B) \sigma_z \xrightarrow{\text{from}} \sigma_y$$

$$\langle \psi_1 | \alpha_z | \psi_1 \rangle = \langle \psi_1 \left(\begin{pmatrix} 0 & \sigma_z \\ \sigma_z & 0 \end{pmatrix} \right) \begin{pmatrix} \text{sgn} B \\ 0 \\ 0 \\ z \end{pmatrix} = \psi_1 \begin{pmatrix} 0 \\ -z \\ \text{sgn} B \\ 0 \end{pmatrix} = 0$$

$$\text{But } \langle \psi_2 | \alpha_z | \psi_1 \rangle = \begin{pmatrix} 0 & \text{sgn} B & -z & 0 \end{pmatrix} \begin{pmatrix} 0 \\ -z \\ \text{sgn} B \\ 0 \end{pmatrix} = -2i \text{sgn} B$$

$$\therefore \langle \psi_2 | v p_2 \alpha_2 | \psi_1 \rangle = -2v p_2 \operatorname{sgn} B ;$$

$$\therefore (v p_2 \alpha_2)_{2 \times 2} = \begin{pmatrix} 0 & +i \\ -i & 0 \end{pmatrix} v p_2 \operatorname{sgn} B = -v p_2 \operatorname{sgn} B \sigma_y$$

(ignoring 2)

$$\therefore \Delta H = v p_y \operatorname{sgn} B \sigma_z - v p_2 \operatorname{sgn} B \sigma_y = v \operatorname{sgn} B (p_y \sigma_z - p_2 \sigma_y)$$

$$= v \operatorname{sgn} B (\vec{p} \times \vec{\sigma})_x$$

But now redefine

$$|\phi_1\rangle = \frac{1}{\sqrt{2}} (|\psi_1\rangle - i|\psi_2\rangle)$$

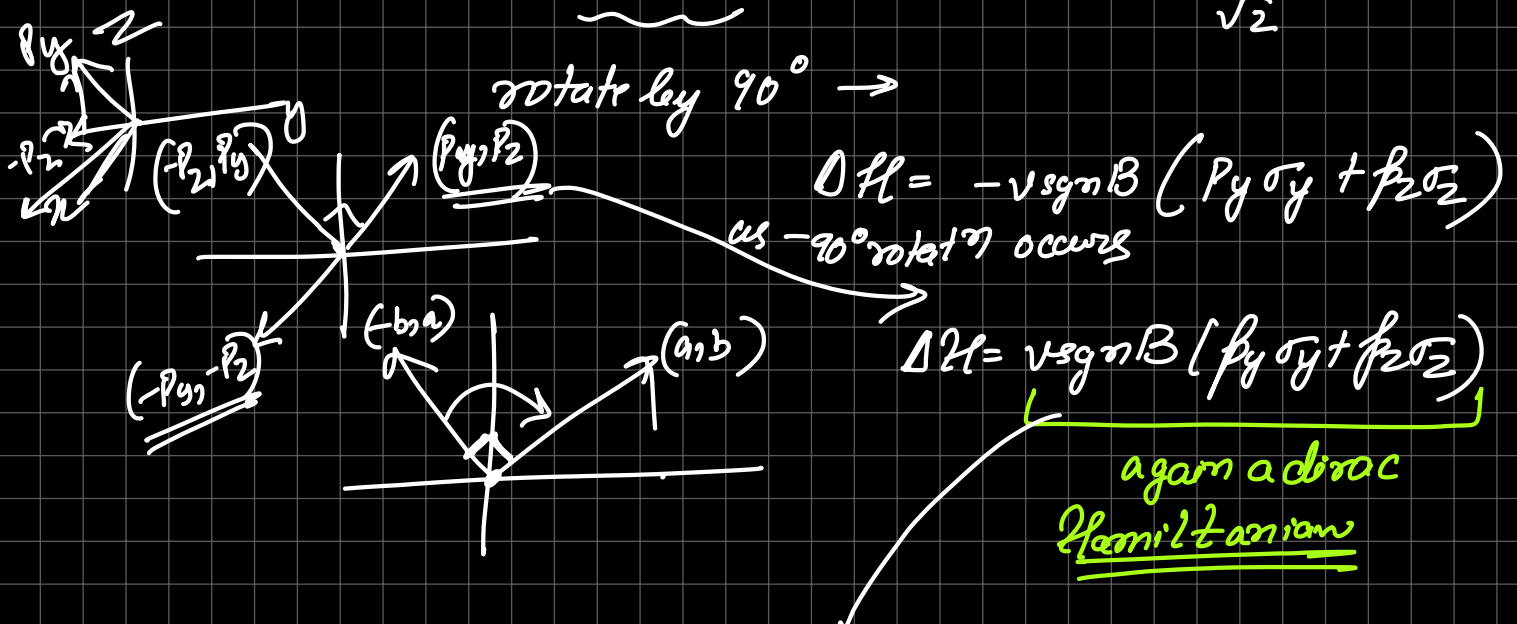
$$|\phi_2\rangle = \frac{-i}{\sqrt{2}} (|\psi_1\rangle + i|\psi_2\rangle)$$

$$\text{or } \begin{pmatrix} \phi_1 \\ \phi_2 \end{pmatrix} = \frac{1}{\sqrt{2}} \underbrace{\begin{pmatrix} 1 & -i \\ -i & +1 \end{pmatrix}}_{\frac{M}{\sqrt{2}}} \begin{pmatrix} |\psi_1\rangle \\ |\psi_2\rangle \end{pmatrix} \Rightarrow \Phi = M \Psi$$

$$\Delta H (\phi_1, \phi_2 \text{ basis}) = \Psi^\dagger \Delta H \Psi = 2 \Psi^\dagger M^\dagger (M \Delta H M^\dagger) M \Psi$$

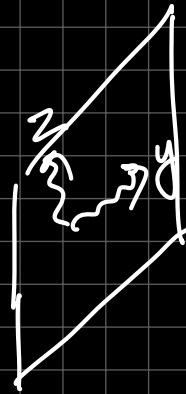
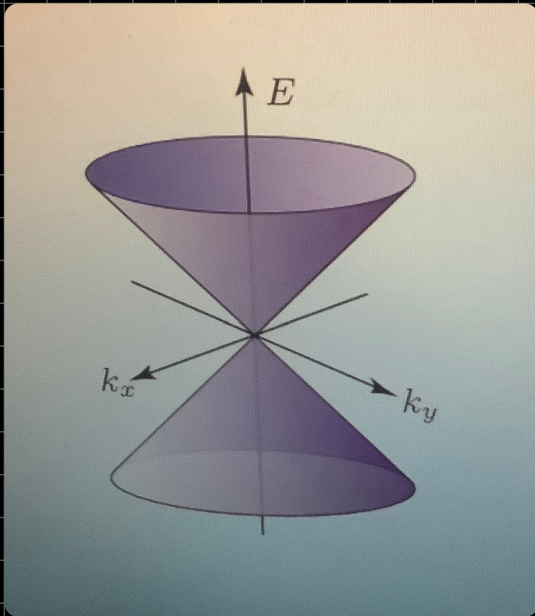
$$\therefore \Delta H \rightarrow M \Delta H M^\dagger$$

$$\text{but } M = \frac{1-i\sigma_z}{\sqrt{2}} = e^{-\frac{i\sigma_z}{2}}$$



$\epsilon_{\pm} = \pm v_F p$, $\beta = \sqrt{p_y^2 + p_z^2} \Rightarrow$ "Dirac like disp., but for a propagating boundary mode"

We get a "Dirac Cone" but for surface states



note:-

- ① σ_i are not "real" spin dof
- ② exact soln

Gapless propagating edge modes

↓
"Dirac like Hamiltonian"
for surface

where

$$\psi_+^0 = \begin{pmatrix} \cos \frac{\theta}{2} \text{sgn}(B) \\ -i \sin \frac{\theta}{2} \text{sgn}(B) \\ \sin \frac{\theta}{2} \\ i \cos \frac{\theta}{2} \end{pmatrix} \quad (2.61)$$

and

$$\psi_-^0 = \begin{pmatrix} \sin \frac{\theta}{2} \text{sgn}(B) \\ i \cos \frac{\theta}{2} \text{sgn}(B) \\ -\cos \frac{\theta}{2} \\ i \sin \frac{\theta}{2} \end{pmatrix} \quad (2.62)$$

with the dispersion relation $\epsilon_{p,\pm} = \pm v_F \text{sgn}(B)$. $\tan \theta = p_y / p_z$. The penetration depth becomes p dependent,

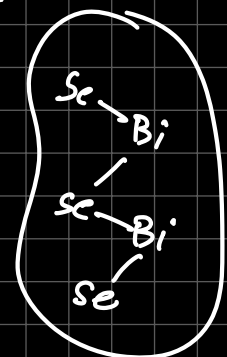
$$\xi_{\pm}^{-1} = \frac{v}{2|B|\hbar} \left(1 \pm \sqrt{1 - 4mB + 4B^2 p^2 / \hbar^2} \right). \quad (2.63)$$

Topological Insulators & Expt relevance

Real material: Bi_2Se_3 — Quintuple layer



only p_z orbitals matter



→ people looked in 3d where a similar "Band inversion" appears. For e.g. Alloys Pb_xSn_{1-x} → x can be tuned to go into int. band situation

$x=0$, one type of symmetry of bands

$x=1$, other type of bands

→ 3d materials (alloys can be used to tune the band)

↳ as function of x , it has band inversion

bulk = insulator

surface = gapless modes

→ Bi_2Se_3 → among the 1st materials to be scanned

↳ by ARPES → shine light on the crystal at a fixed relative angle & look at

Allows you to map band structure
↓
measure "filled states"

the outgoing electron
↓
can detect its $\vec{k}$ & Energy of it.

→ Bi_2Se_3 → known to be SC for a lot of time

↳ but inside the gap, ∃ a few states (edge states)

↓
"they saw cones touching each other"

↳ $0 \sim 50$ meV where it's valid.

dispersion of surface state looks like $\hbar \sim (\sigma_x p_x + \sigma_y p_y)$ [as our calc]

Diff from graphene ⇒ no info about spin
→ but here the $\hbar_{surface}$ has info

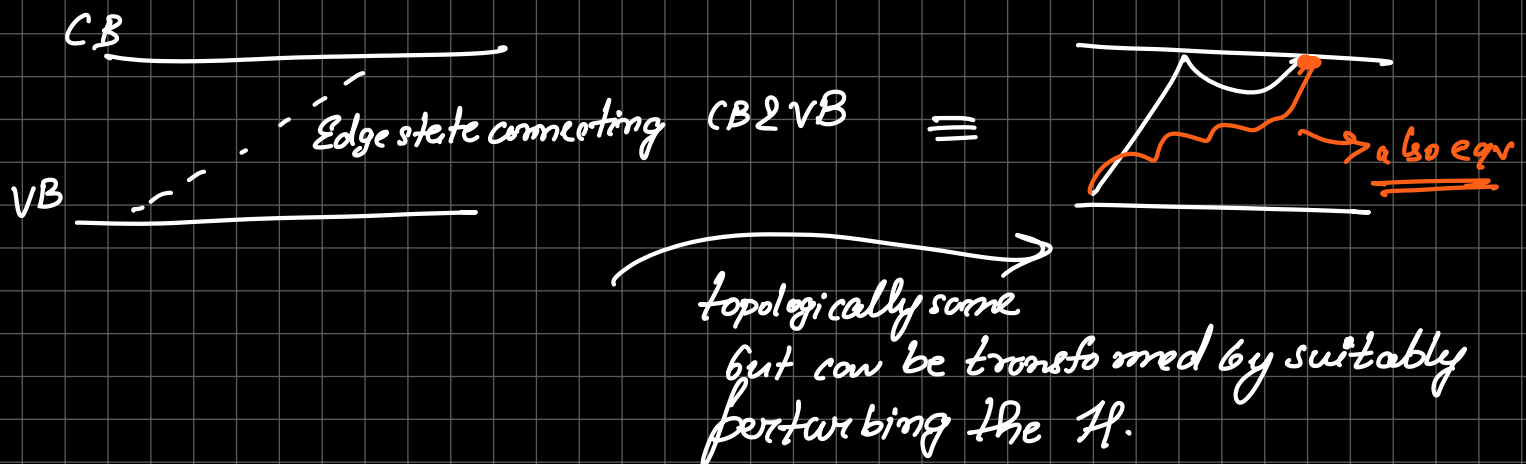
spin is coupled $\longleftrightarrow$ about spin of the electrons.
to momenta $\longrightarrow$ spin resolved photoemission spectroscopy
can give info about
spin resolved bandstructure.

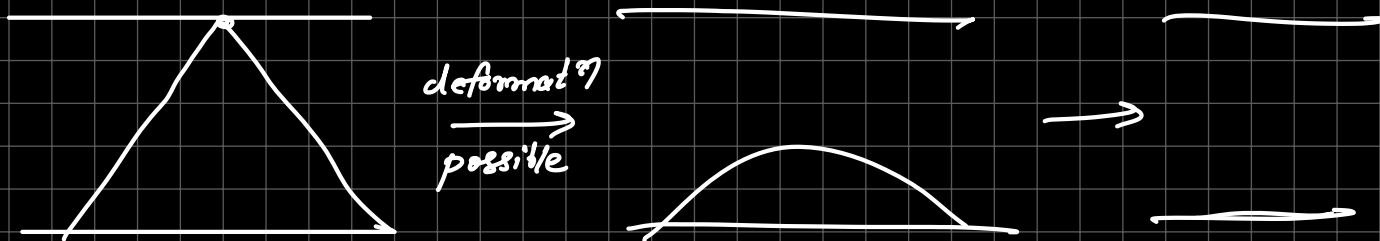
$\neg$ (in real materials) even/odd # of dirac cones.

for even, it's
not a strong topological
insulator as even #
can be roughly equated to
having no cones in
Bandstructure.

odd
 $\rightarrow$ strong topo. insulator
 $\rightarrow$ cannot make the
dirac cones disappear

Check:- Vanderbilt's book for
a discussion of the invariance
of topological systems.

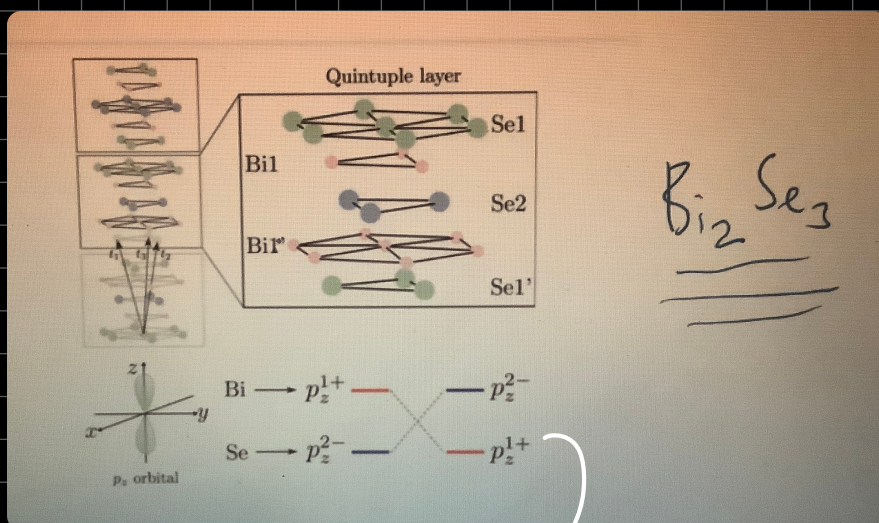




even # of
Dirac cones

Q. How is the deformation done exactly?
 $\rightarrow$ "Z₂ index" related to it
 $\hookrightarrow$

Bi₂Se₃



Bi₂Se₃

coupling b/w ~~quintuple~~
 Quintuple layers is
 vdw (2 weak) but
 intra layer is strong

have "partially
 filled" p_z orbitals $\rightarrow$ imp for what happens
 close to Fermi energy.

"inversion symmetry present"

• Basis: Close to Fermi energy

$|p_z^{1+}, \uparrow\rangle, |p_z^{1+}, \downarrow\rangle, |p_z^{2-}, \uparrow\rangle, |p_z^{2-}, \downarrow\rangle$

$\swarrow$
 $\text{Bi}_2\text{Se}_3 \rightarrow$ large Z_2 , so large SOC & hence
 spin attributed basis is chosen. (probably spin polarized)

The effective hamiltonian

$$H = E(p) + \sum_{i=1,2,3} v_i p_i \alpha_i + (M - \sum p_i^2) \beta$$

$$E(p) = -D_{||} (\underline{p_x^2 + p_y^2}) - D_{\perp} p_z^2$$

→ Heuristics → • A gen decomp into α_i, β is ofc possible, H being 4×4

• now wkt TRS is present, we apply $\vec{k} \cdot \vec{p} \rightarrow$



$$\alpha_i \xrightarrow{\text{TRS}} -\alpha_i$$

$\beta \xrightarrow{\text{TRS}} \beta$ → pair with odd terms in momentum.

→ pair with even terms of β

in $\vec{k} \cdot \vec{p}$,
you'll get
terms like

$$\epsilon_{mn} + \frac{p^2}{2 \cdot m}$$

demand $f(\vec{k})$ be odd under TRS

gives rise to $v p_i \alpha_i$ type terms

give rise to βp^2 terms of H .

/ side note:- Kane & Mele → Gaps out Graphene & introduces SOC
→ ribbon geo was done in lecture]

→ @ Shoucheng Zhang ⇒ used $\text{HgTe} - \text{CdTe} \rightarrow$ bands inverted

"at the edges, the mode is topological"

→ Graphene (weak SOC) when put on an insulator (strong SOC)

(can be proximitized to have a strong SOC.

→ probably

none

can be

realized on it

but

Bi₂Se₃ also generates
an eqv model.